

MOSFETs Silicon N-Channel MOS

# SSM3K59CTB

#### 1. Applications

· DC-DC Converters

#### 2. Features

- (1) 1.8-V gate drive voltage.
- (2) Low drain-source on-resistance

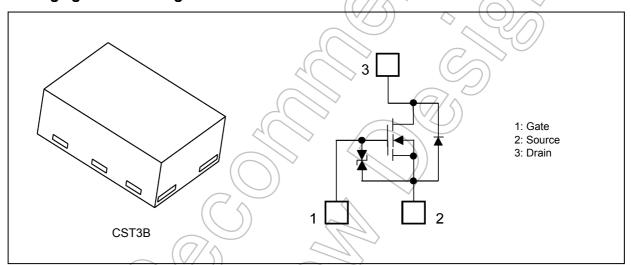
 $R_{DS(ON)} = 250 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 1.8 \text{ V}, I_D = 0.2 \text{ A})$ 

 $R_{DS(ON)} = 210 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 2.5 \text{ V}, I_D = 0.5 \text{ A})$ 

 $R_{\rm DS(ON)} = 185~{\rm m}\Omega$  (typ.) (@ $V_{\rm GS} = 4.5~{\rm V},~I_{\rm D} = 1.0~{\rm A}$ )

 $R_{DS(ON)} = 175 \text{ m}\Omega \text{ (typ.)} (@V_{GS} = 8.0 \text{ V}, I_D = 1.0 \text{ A})$ 

#### 3. Packaging and Pin Assignment



## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	40	V
Gate-source voltage		V <sub>GSS</sub>	±12	
Drain current (DC)	(Note 1)	I <sub>D</sub>	2.0	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	4.0	
Power dissipation	(Note 2)	P <sub>D</sub>	1000	mW
Channel temperature		T <sub>ch</sub>	150	ů
Storage temperature		T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

Start of commercial production

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat discipation fully into account.





#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_		±10	μΑ
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0V		_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	40			V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -12 V	25	7		V
Gate threshold voltage	(Note 2)	$V_{th}$	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1 mA	0.5	)_	1.2	V
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 8.0 V	/ <del>(</del> )	175	215	mΩ
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.5 V		185	228	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 4.2 V	> -	186	231	
			I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 3.6 V	_	190	238	
			I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 2.5 V	_	210	268	
			I <sub>D</sub> = 0.2 A, V <sub>GS</sub> = 1.8 V	- ,	250	420	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_{D} = 200 \text{ mA}$	-6	2	> -	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drain-source breakdown voltage is lowered in this mode.

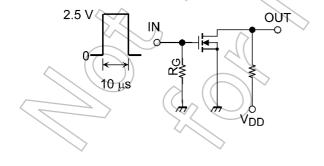
Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	Ciss	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	_	130	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	7.5	_	
Output capacitance	C <sub>oss</sub>		_	26	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD} = 10 \text{ V}, I_{D} = 0.5 \text{ A},$	_	13	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 4.7 $\Omega$	_	8	_	

#### 5.3. Switching Time Test Circuit





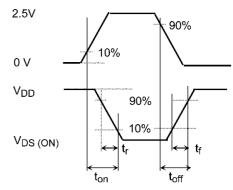


Fig. 5.3.2 Input Waveform/Output Waveform



## 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} = 10 \text{ V}, I_D = 1.8 \text{ A},$	_	1.1	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{GS} = 4.2 \text{ V}$	_	0.18	_	
Gate-drain charge	Q <sub>gd</sub>		<u> </u>	0.5	_	

## 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = 0 V	((// \( \)	-0.85	-1.2	V

Note 1: Pulse measurement.

### 6. Marking



Fig. 6.1 Marking

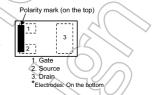


Fig. 6.2 Pin Condition (top view)



### 7. Characteristics Curves (Note)

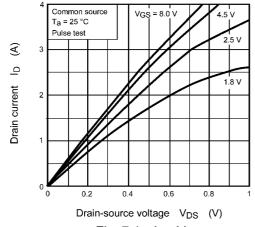


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

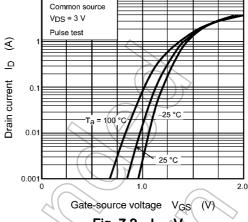


Fig. 7.2 ID - VGS

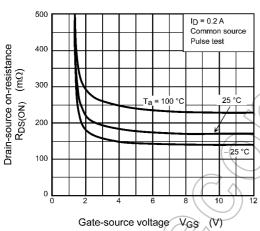


Fig. 7.3 RDS(ON) - VGS

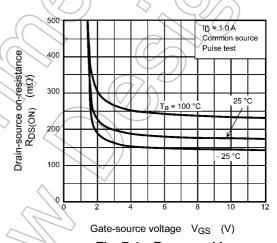


Fig. 7.4  $R_{DS(ON)}$  -  $V_{GS}$ 

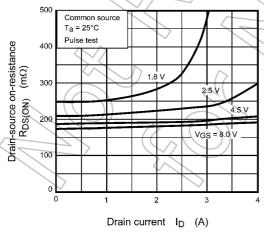


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

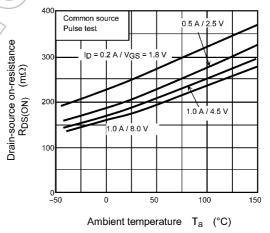
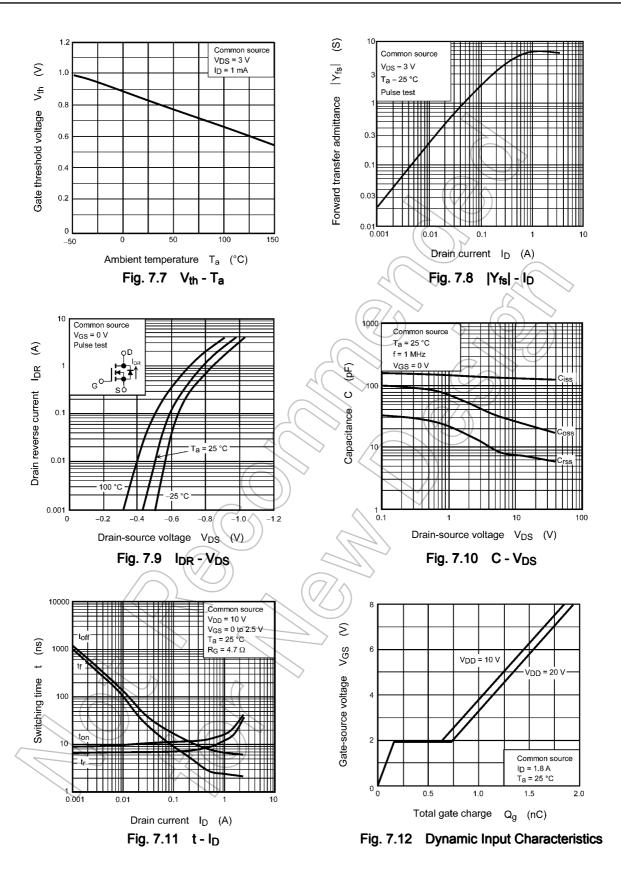
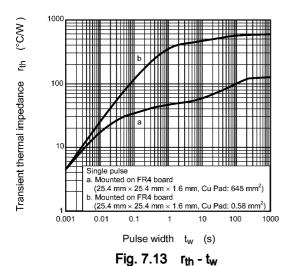


Fig. 7.6 RDS(ON) - Ta





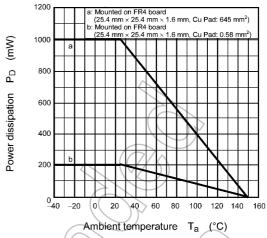
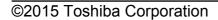


Fig. 7.14 PD - Ta

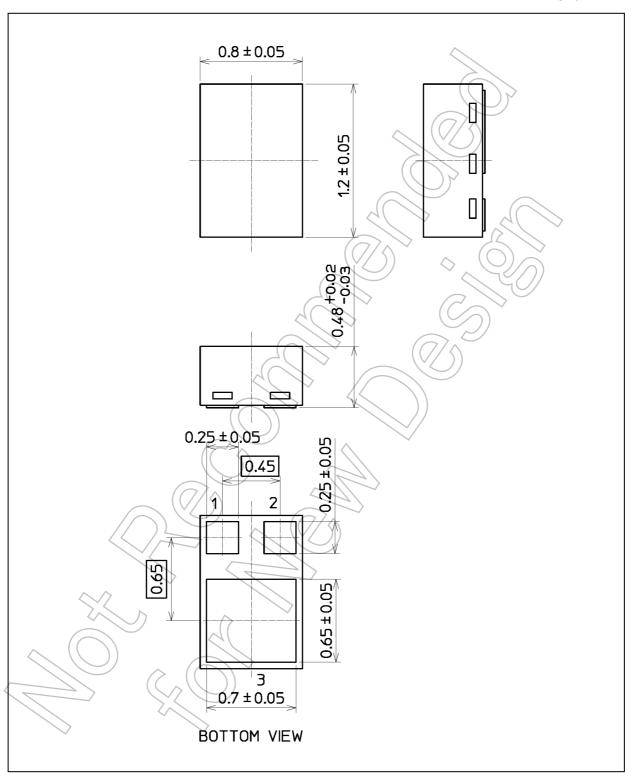
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.





## **Package Dimensions**

Unit: mm



Weight: 0.75 mg (typ.)

	Package Name(s)
Nickname: CST3B	



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